

Complementary Plastic Silicon Power Transistors

... designed for low power audio amplifier and low-current, high speed switching applications.

- High Collector–Emitter Sustaining Voltage —
 $V_{CEO(sus)} = 80 \text{ Vdc (Min) — BD789, BD790}$
 $= 100 \text{ Vdc (Min) — BD791, BD792}$
- High DC Current Gain @ $I_C = 200 \text{ mAdc}$
 $h_{FE} = 40\text{--}250$
- Low Collector–Emitter Saturation Voltage —
 $V_{CE(sat)} = 0.5 \text{ Vdc (Max) @ } I_C = 500 \text{ mAdc}$
- High Current Gain — Bandwidth Product —
 $f_T = 40 \text{ MHz (Min) @ } I_C = 100 \text{ mAdc}$

*MAXIMUM RATINGS

Rating	Symbol	BD789 BD790	BD791 BD792	Unit
Collector–Emitter Voltage	V_{CEO}	80	100	Vdc
Collector–Base Voltage	V_{CB}	80	100	Vdc
Emitter–Base Voltage	V_{EBO}	6.0		Vdc
Collector Current — Continuous — Peak	I_C	4.0 8.0		Adc
Base Current	I_B	1.0		Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	15 0.12		Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–65 to +150		$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	8.34	$^\circ\text{C/W}$

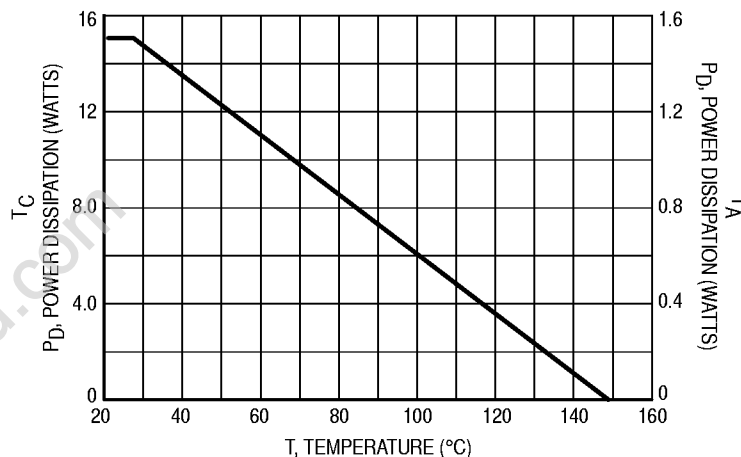


Figure 1. Power Derating

Preferred devices are Motorola recommended choices for future use and best overall value.

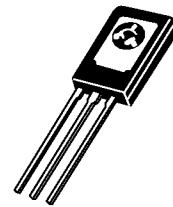
REV 7



NPN
BD789
BD791*
PNP
BD790
BD792*

*Motorola Preferred Device

4 AMPERE
POWER TRANSISTORS
COMPLEMENTARY
SILICON
80, 100 VOLTS
15 WATTS



CASE 77–08
TO–225AA TYPE

BD789 BD791 BD790 BD792

*ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (1) ($I_C = 10\text{ mAdc}$, $I_B = 0$)	BD789, BD790 BD791, BD792	$V_{CEO(sus)}$	80 100	— —	Vdc
Collector Cutoff Current ($V_{CE} = 40\text{ Vdc}$, $I_B = 0$) ($V_{CE} = 50\text{ Vdc}$, $I_B = 0$)	BD789, BD790 BD791, BD792	I_{CEO}	— —	100 100	μAdc
Collector Cutoff Current ($V_{CE} = 80\text{ Vdc}$, $V_{BE(off)} = 1.5\text{ Vdc}$) ($V_{CE} = 100\text{ Vdc}$, $V_{BE(off)} = 1.5\text{ Vdc}$) ($V_{CE} = 40\text{ Vdc}$, $V_{BE(off)} = 1.5\text{ Vdc}$, $T_C = 125^\circ\text{C}$) ($V_{CE} = 50\text{ Vdc}$, $V_{BE(off)} = 1.5\text{ Vdc}$, $T_C = 125^\circ\text{C}$)	BD789, BD790 BD791, BD792 BD789, BD790 BD791, BD792	I_{CEX}	— — — —	1.0 1.0 0.1 0.1	μAdc mAdc
Emitter Cutoff Current ($V_{EB} = 6.0\text{ Vdc}$, $I_C = 0$)		I_{EBO}	—	1.0	μAdc
ON CHARACTERISTICS (1)					
DC Current Gain ($I_C = 200\text{ mAdc}$, $V_{CE} = 3.0\text{ Vdc}$) ($I_C = 1.0\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$) ($I_C = 2.0\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$) ($I_C = 4.0\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$)		h_{FE}	40 20 10 5.0	250 — — —	—
Collector Emitter Saturation Voltage ($I_C = 500\text{ mAdc}$, $I_B = 50\text{ mAdc}$) ($I_C = 1.0\text{ Adc}$, $I_B = 100\text{ mAdc}$) ($I_C = 2.0\text{ Adc}$, $I_B = 200\text{ mAdc}$) ($I_C = 4.0\text{ Adc}$, $I_B = 800\text{ mAdc}$)		$V_{CE(sat)}$	— — — —	0.5 1.0 2.5 3.0	Vdc
Base–Emitter Saturation Voltage ($I_C = 2.0\text{ Adc}$, $I_B = 200\text{ mAdc}$)		$V_{BE(sat)}$	—	1.8	Vdc
Base–Emitter On Voltage ($I_C = 200\text{ mAdc}$, $V_{CE} = 3.0\text{ Vdc}$)		$V_{BE(on)}$	—	1.5	Vdc
DYNAMIC CHARACTERISTICS					
Current–Gain — Bandwidth Product ($I_C = 100\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 10\text{ MHz}$)		f_T	40	—	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_C = 0$, $f = 0.1\text{ MHz}$)	BD789, BD791 BD790, BD792	C_{ob}	— —	50 70	pF
Small–Signal Current Gain ($I_C = 200\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)		h_{fe}	10	—	—

* Indicates JEDEC Registered Data.

(1) Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

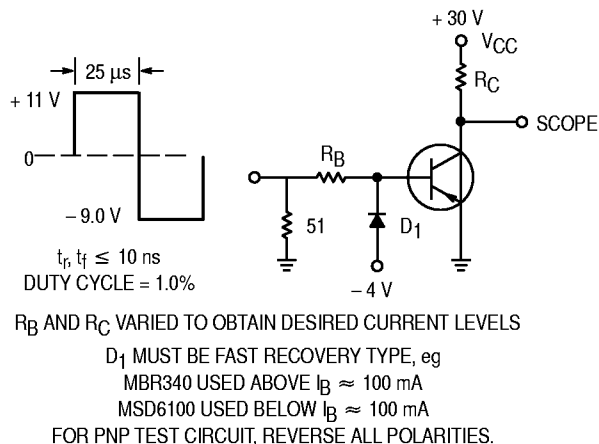


Figure 2. Switching Time Test Circuit

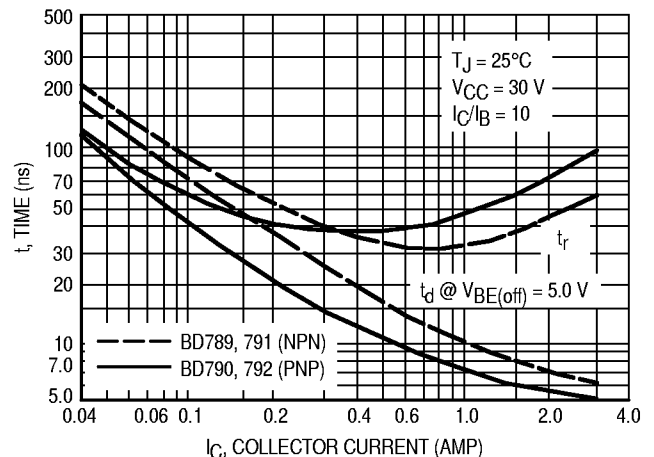


Figure 3. Turn–On Time

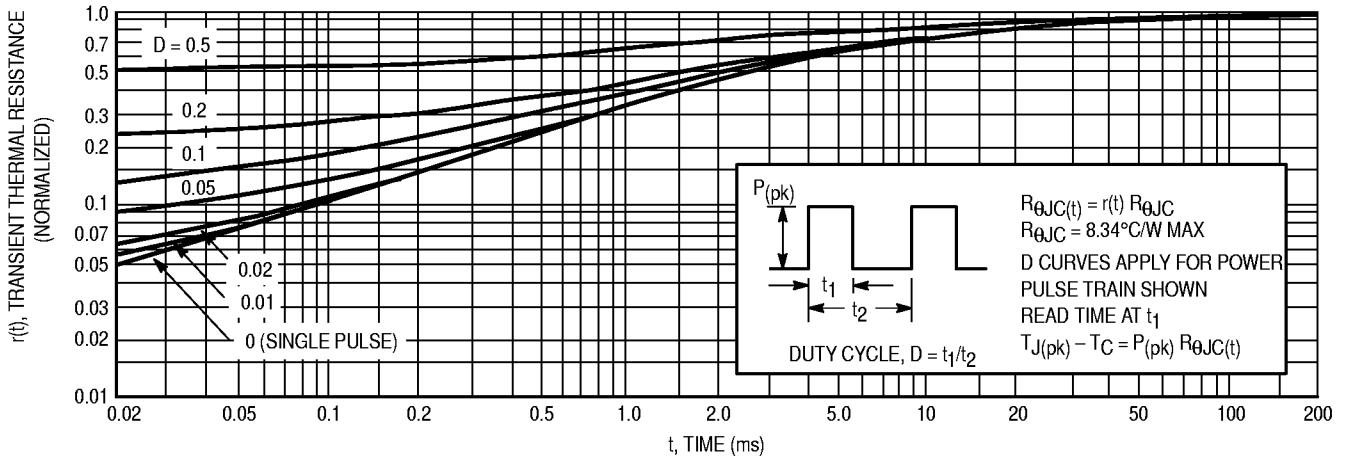


Figure 4. Thermal Response

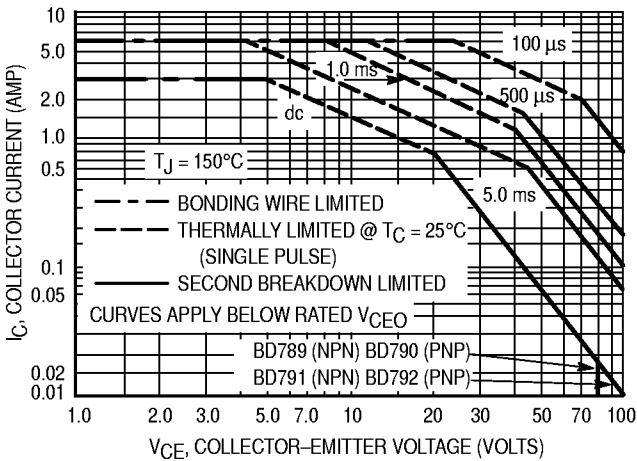


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^\circ\text{C}$: T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^\circ\text{C}$, $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

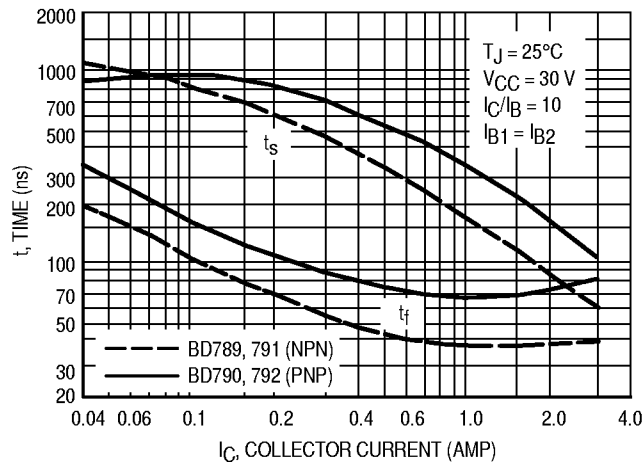


Figure 6. Turn-Off Time

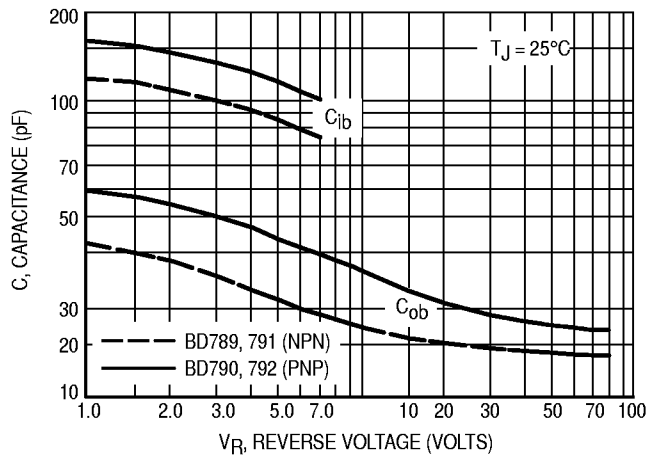


Figure 7. Capacitance

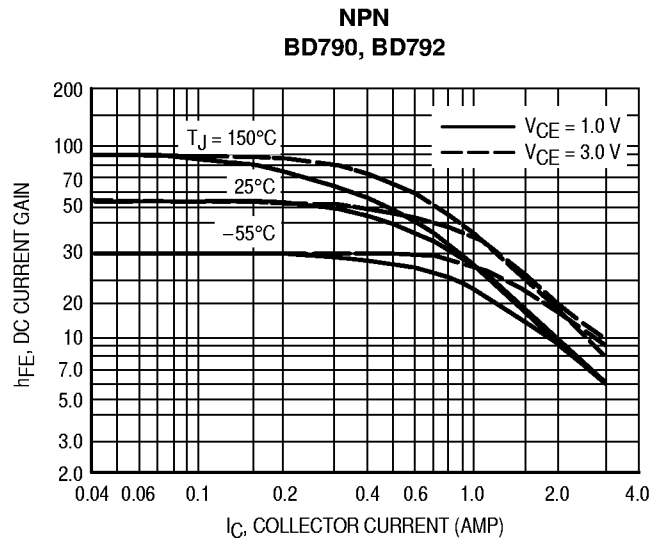
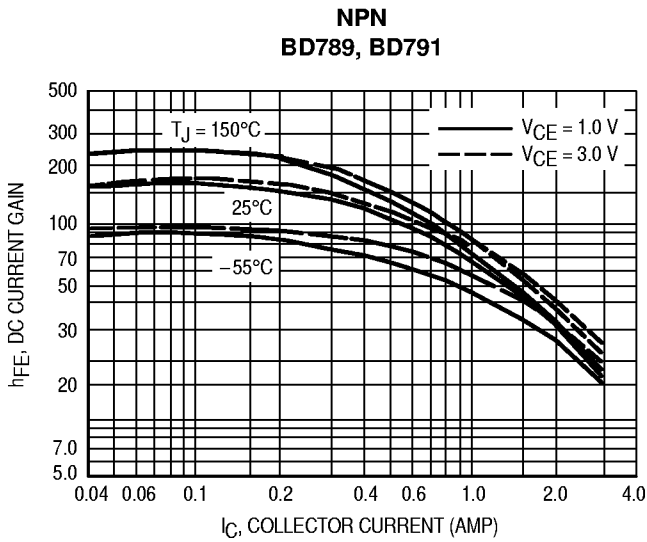


Figure 8. DC Current Gain

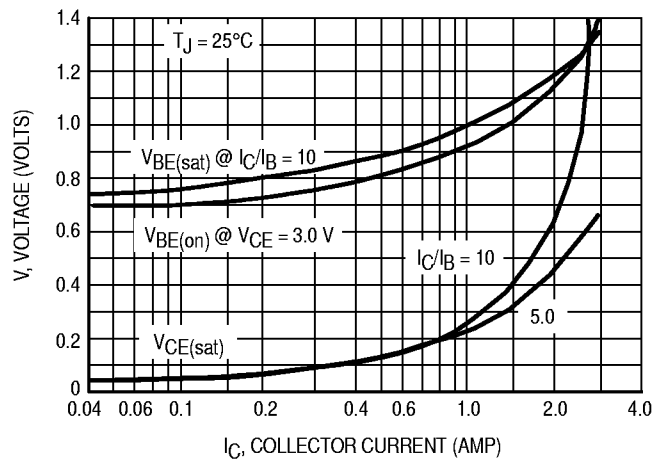
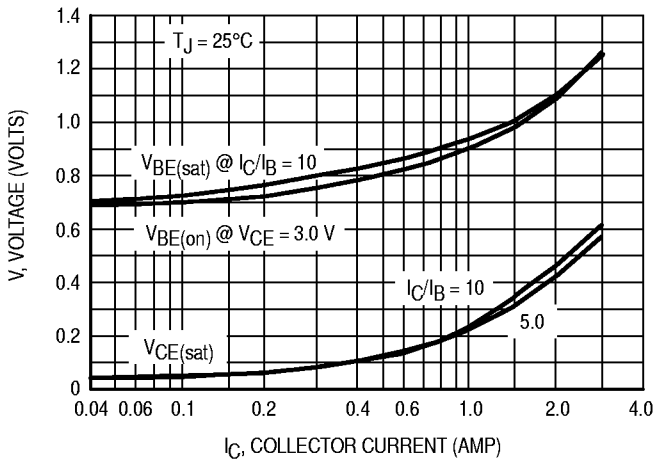


Figure 9. "On" Voltages

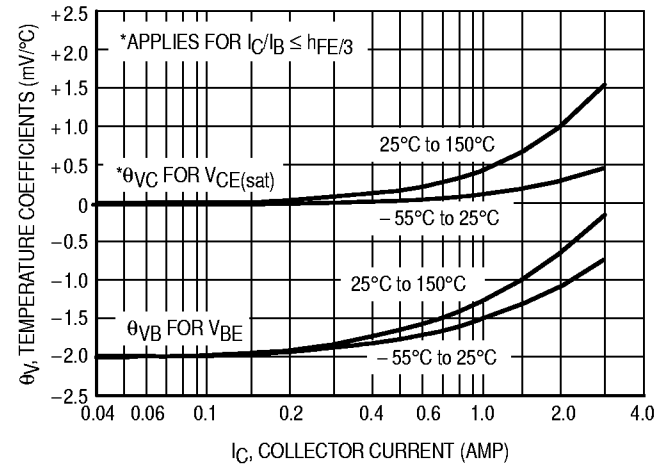
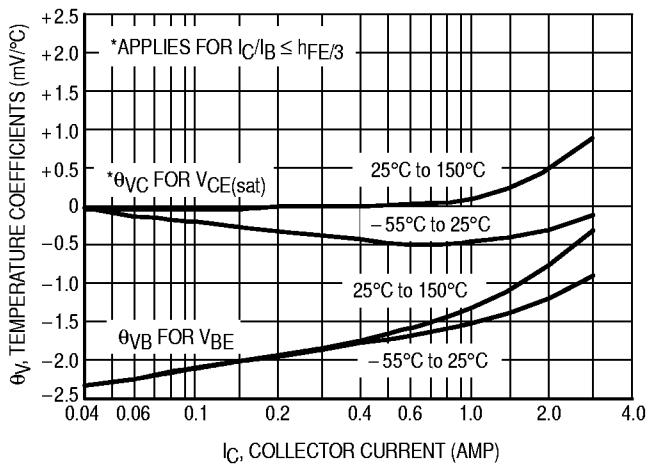
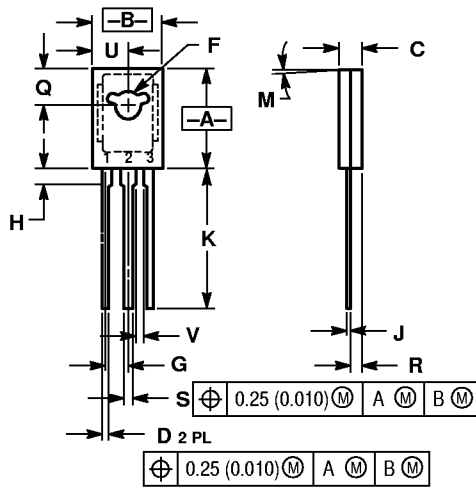


Figure 10. Temperature Coefficients

PACKAGE DIMENSIONS



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.055	1.15	1.39
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	—	1.02	—

- STYLE 1:
 PIN 1. EMITTER
 2. COLLECTOR
 3. BASE

CASE 77-08
 TO-225AA TYPE
 ISSUE V